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Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560c50l3c6e0y

Table 2. SPC560B40x/50x and SPC560C40x/50x device comparison⁽¹⁾ (continued)

Feature	Device										
	SPC560B 40L1	SPC560B 40L3	SPC560B 40L5	SPC560C 40L1	SPC560C 40L3	SPC560B 50L1	SPC560B 50L3	SPC560B 50L5	SPC560C 50L1	SPC560C 50L3	SPC560B 50B2
Debug	JTAG										Nexus2+
Package	LQFP64 ⁽⁹⁾	LQFP100	LQFP144	LQFP64 ⁽⁹⁾	LQFP100	LQFP64 ⁽⁹⁾	LQFP100	LQFP144	LQFP64 ⁽⁹⁾	LQFP100	LBGA208 ⁽¹⁰⁾

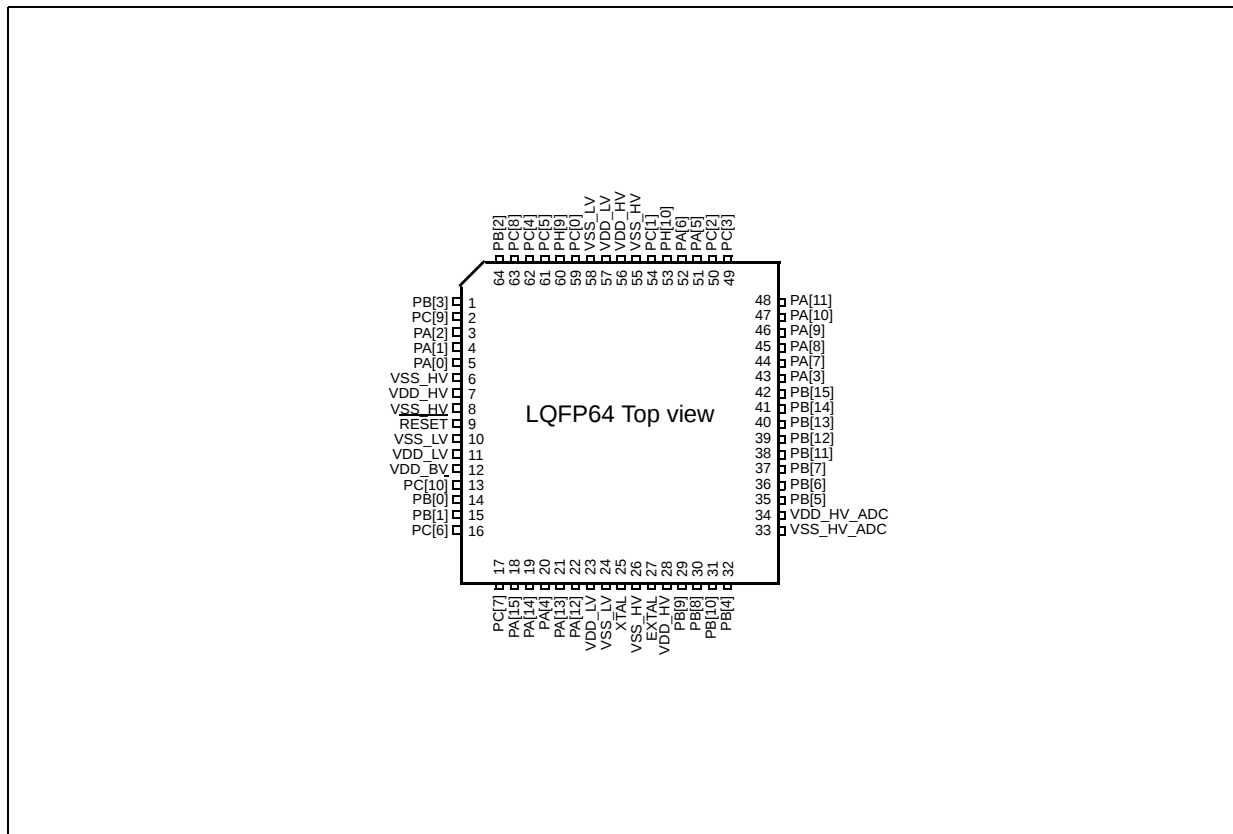
1. Feature set dependent on selected peripheral multiplexing—table shows example implementation.
2. Based on 125 °C ambient operating temperature.
3. See the eMIOS section of the device reference manual for information on the channel configuration and functions.
4. IC – Input Capture; OC – Output Compare; PWM – Pulse Width Modulation; MC – Modulus counter.
5. SCI0, SCI1 and SCI2 are available. SCI3 is not available.
6. CAN0, CAN1 are available. CAN2, CAN3, CAN4 and CAN5 are not available.
7. CAN0, CAN1 and CAN2 are available. CAN3, CAN4 and CAN5 are not available.
8. I/O count based on multiplexing with peripherals.
9. All LQFP64 information is indicative and must be confirmed during silicon validation.
10. LBGA208 available only as development package for Nexus2+.

3 Package pinouts and signal descriptions

3.1 Package pinouts

The available LQFP pinouts and the LPGA208 ballmap are provided in the following figures. For pin signal descriptions, please refer to the device reference manual (RM0017).

Figure 2. LQFP 64-pin configuration^(a)



a. All LQFP64 information is indicative and must be confirmed during silicon validation.

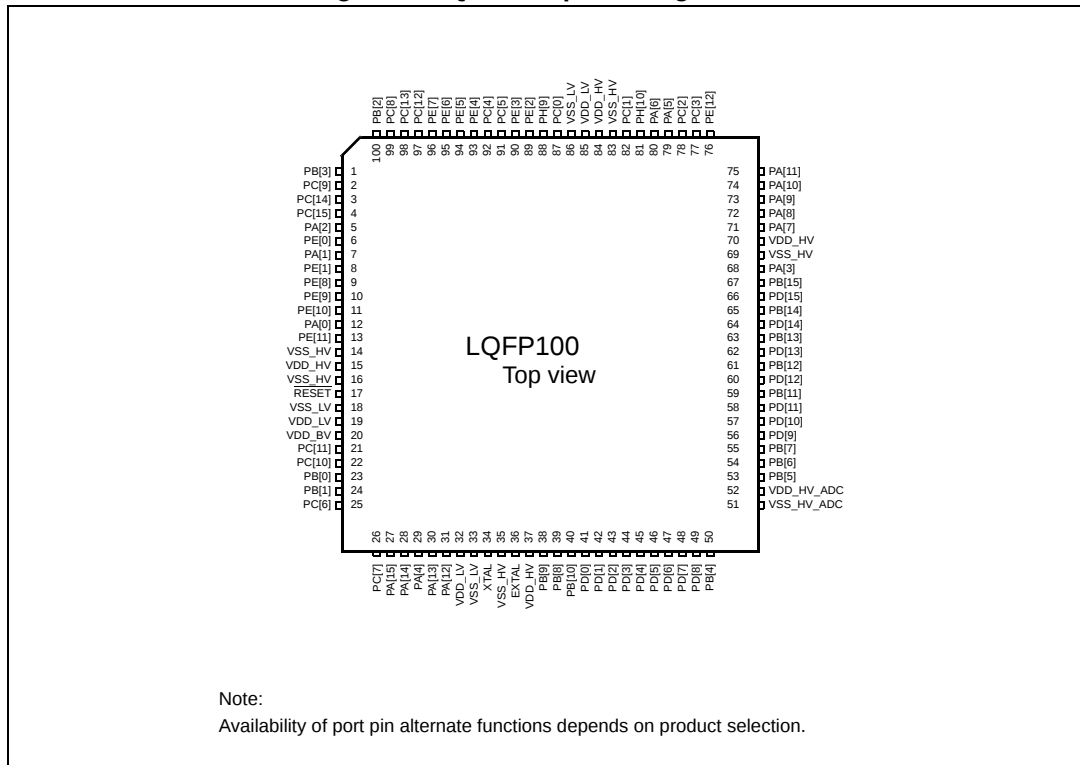


Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PB[5]	PCR[21]	AF0 AF1 AF2 AF3 —	GPIO[21] — — — GPI[1]	SIUL — — — ADC	I — — — I	I	Tristate	35	53	75	R16
PB[6]	PCR[22]	AF0 AF1 AF2 AF3 —	GPIO[22] — — — GPI[2]	SIUL — — — ADC	I — — — I	I	Tristate	36	54	76	P15
PB[7]	PCR[23]	AF0 AF1 AF2 AF3 —	GPIO[23] — — — GPI[3]	SIUL — — — ADC	I — — — I	I	Tristate	37	55	77	P16
PB[8]	PCR[24]	AF0 AF1 AF2 AF3 — —	GPIO[24] — — — — ANS[0] OSC32K_XTAL ⁽⁷⁾	SIUL — — — — ADC SXOSC	I — — — — I I/O	I	Tristate	30	39	53	R9
PB[9]	PCR[25]	AF0 AF1 AF2 AF3 — —	GPIO[25] — — — — ANS[1] OSC32K_EXTAL ⁽⁷⁾	SIUL — — — — ADC SXOSC	I — — — — I I/O	I	Tristate	29	38	52	T9
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — —	GPIO[26] — — — — ANS[2] WKPU[8] ⁽⁴⁾	SIUL — — — — ADC WKPU	I/O — — — — I I	J	Tristate	31	40	54	P9

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PB[11] (8)	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ANS[3]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — I/O I	J	Tristate	38	59	81	N13
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ANX[0]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	39	61	83	M16
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ANX[1]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	40	63	85	M13
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ANX[2]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	41	65	87	L16
PB[15]	PCR[31]	AF0 AF1 AF2 AF3 —	GPIO[31] E0UC[7] — CS4_0 ANX[3]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	42	67	89	L13
PC[0] ⁽⁹⁾	PCR[32]	AF0 AF1 AF2 AF3	GPIO[32] — TDI —	SIUL — JTAGC —	I/O — I —	M	Input, weak pull-up	59	87	126	A8
PC[1] ⁽⁹⁾	PCR[33]	AF0 AF1 AF2 AF3	GPIO[33] — TDO ⁽¹⁰⁾ —	SIUL — JTAGC —	I/O — O —	M	Tristate	54	82	121	C9

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PC[15]	PCR[47]	AF0 AF1 AF2 AF3	GPIO[47] E0UC[15] CS0_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O I/O —	M	Tristate	—	4	4	D3
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 —	GPIO[48] — — — GPI[4]	SIUL — — — ADC	I — — — I	I	Tristate	—	41	63	P12
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 —	GPIO[49] — — — GPI[5]	SIUL — — — ADC	I — — — I	I	Tristate	—	42	64	T12
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 —	GPIO[50] — — — GPI[6]	SIUL — — — ADC	I — — — I	I	Tristate	—	43	65	R12
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 —	GPIO[51] — — — GPI[7]	SIUL — — — ADC	I — — — I	I	Tristate	—	44	66	P13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 —	GPIO[52] — — — GPI[8]	SIUL — — — ADC	I — — — I	I	Tristate	—	45	67	R13
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 —	GPIO[53] — — — GPI[9]	SIUL — — — ADC	I — — — I	I	Tristate	—	46	68	T13

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ⁽¹⁾	Function	Peripheral	I/O direction ⁽²⁾	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208 ⁽³⁾
PG[0]	PCR[96]	AF0 AF1 AF2 AF3	GPIO[96] CAN5TX ⁽¹¹⁾ E1UC[23] —	SIUL FlexCAN_5 eMIOS_1 —	I/O O I/O —	M	Tristate	—	—	98	E14
PG[1]	PCR[97]	AF0 AF1 AF2 AF3 — —	GPIO[97] — E1UC[24] — CAN5RX ⁽¹¹⁾ EIRQ[14]	SIUL — eMIOS_1 — FlexCAN_5 SIUL	I/O — I/O — I I	S	Tristate	—	—	97	E13
PG[2]	PCR[98]	AF0 AF1 AF2 AF3	GPIO[98] E1UC[11] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	8	E4
PG[3]	PCR[99]	AF0 AF1 AF2 AF3 —	GPIO[99] E1UC[12] — — WKPU[17] ⁽⁴⁾	SIUL eMIOS_1 — — WKPU	I/O I/O — — I	S	Tristate	—	—	7	E3
PG[4]	PCR[100]	AF0 AF1 AF2 AF3	GPIO[100] E1UC[13] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	6	E1
PG[5]	PCR[101]	AF0 AF1 AF2 AF3 —	GPIO[101] E1UC[14] — — WKPU[18] ⁽⁴⁾	SIUL eMIOS_1 — — WKPU	I/O I/O — — I	S	Tristate	—	—	5	E2
PG[6]	PCR[102]	AF0 AF1 AF2 AF3	GPIO[102] E1UC[15] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	—	30	M2

Table 13. Recommended operating conditions (3.3 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	$V_{SS}-0.1$	—	V
			Relative to V_{DD}	—	$V_{DD}+0.1$	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	-5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	-50	50	
TV_{DD}	SR	V_{DD} slope to ensure correct power up ⁽⁶⁾	—	3.0 ⁽⁷⁾	250×10^3 (0.25 [V/ μ s])	V/s

- 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair
- 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.
- 400 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).
- 100 nF capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair.
- Full electrical specification cannot be guaranteed when voltage drops below 3.0 V. In particular, ADC electrical characteristics and I/Os DC electrical specification may not be guaranteed. When voltage drops below V_{LVDHVL} , device is reset.
- Guaranteed by device validation.
- Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

Table 14. Recommended operating conditions (5.0 V)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{SS}	SR	Digital ground on V_{SS_HV} pins	—	0	0	V
$V_{DD}^{(1)}$	SR	Voltage on V_{DD_HV} pins with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
$V_{SS_LV}^{(3)}$	SR	Voltage on V_{SS_LV} (low voltage digital supply) pins with respect to ground (V_{SS})	—	$V_{SS}-0.1$	$V_{SS}+0.1$	V
$V_{DD_BV}^{(4)}$	SR	Voltage on V_{DD_BV} pin (regulator supply) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
			Relative to V_{DD}	$V_{DD}-0.1$	$V_{DD}+0.1$	
V_{SS_ADC}	SR	Voltage on $V_{SS_HV_ADC}$ (ADC reference) pin with respect to ground (V_{SS})	—	$V_{SS}-0.1$	$V_{SS}+0.1$	V
$V_{DD_ADC}^{(5)}$	SR	Voltage on $V_{DD_HV_ADC}$ pin (ADC reference) with respect to ground (V_{SS})	—	4.5	5.5	V
			Voltage drop ⁽²⁾	3.0	5.5	
			Relative to V_{DD}	$V_{DD}-0.1$	$V_{DD}+0.1$	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS})	—	$V_{SS}-0.1$	—	V
			Relative to V_{DD}	—	$V_{DD}+0.1$	

2. The configuration PAD3V5 = 1 when $V_{DD} = 5\text{ V}$ is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 20. FAST configuration output buffer electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V_{OH}	CC	Output high level FAST configuration	Push Pull	$I_{OH} = -14\text{mA}$, $V_{DD} = 5.0\text{ V} \pm 10\%$, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	V
				$I_{OH} = -7\text{mA}$, $V_{DD} = 5.0\text{ V} \pm 10\%$, PAD3V5V = 1 ⁽²⁾	$0.8V_{DD}$	—	
				$I_{OH} = -11\text{mA}$, $V_{DD} = 3.3\text{ V} \pm 10\%$, PAD3V5V = 1 (recommended)	$V_{DD}-0.8$	—	
V_{OL}	CC	Output low level FAST configuration	Push Pull	$I_{OL} = 14\text{mA}$, $V_{DD} = 5.0\text{ V} \pm 10\%$, PAD3V5V = 0 (recommended)	—	$0.1V_{DD}$	V
				$I_{OL} = 7\text{mA}$, $V_{DD} = 5.0\text{ V} \pm 10\%$, PAD3V5V = 1 ⁽²⁾	—	$0.1V_{DD}$	
				$I_{OL} = 11\text{mA}$, $V_{DD} = 3.3\text{ V} \pm 10\%$, PAD3V5V = 1 (recommended)	—	0.5	

1. $V_{DD} = 3.3\text{ V} \pm 10\%$ / $5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$, unless otherwise specified

2. The configuration PAD3V5 = 1 when $V_{DD} = 5\text{ V}$ is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

3.15.4 Output pin transition times

Table 21. Output pin transition times

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
t_{tr}	CC	Output transition time output pin ⁽²⁾ SLOW configuration	$C_L = 25\text{ pF}$	$V_{DD} = 5.0\text{ V} \pm 10\%$, PAD3V5V = 0	—	50	ns
			$C_L = 50\text{ pF}$		—	100	
			$C_L = 100\text{ pF}$		—	125	
			$C_L = 25\text{ pF}$	$V_{DD} = 3.3\text{ V} \pm 10\%$, PAD3V5V = 1	—	50	
			$C_L = 50\text{ pF}$		—	100	
			$C_L = 100\text{ pF}$		—	125	

Figure 7. Start-up reset requirements

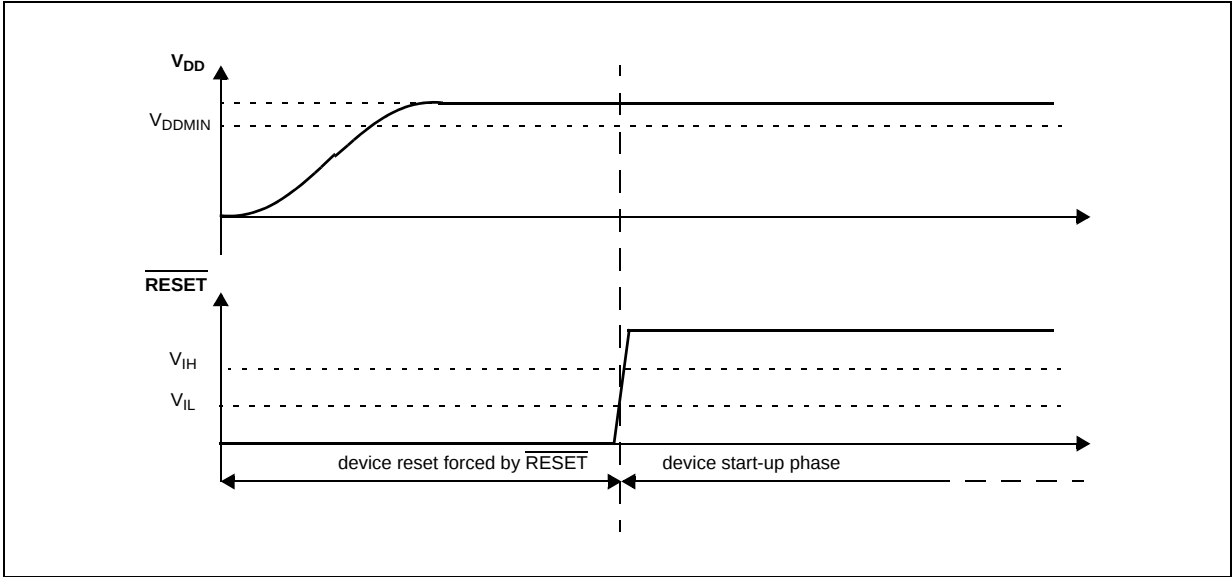


Figure 8. Noise filtering on reset signal

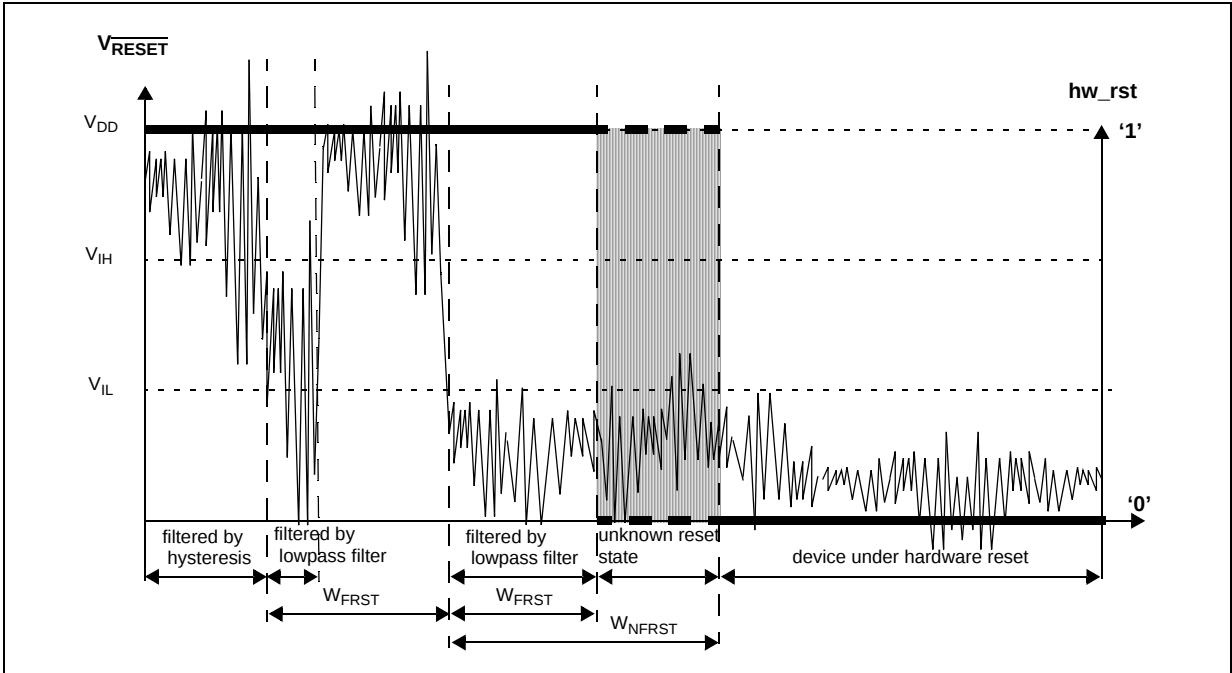


Table 25. Reset electrical characteristics

Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	$0.65V_{DD}$	—	$V_{DD}+0.4$	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	-0.4	—	$0.35V_{DD}$	V

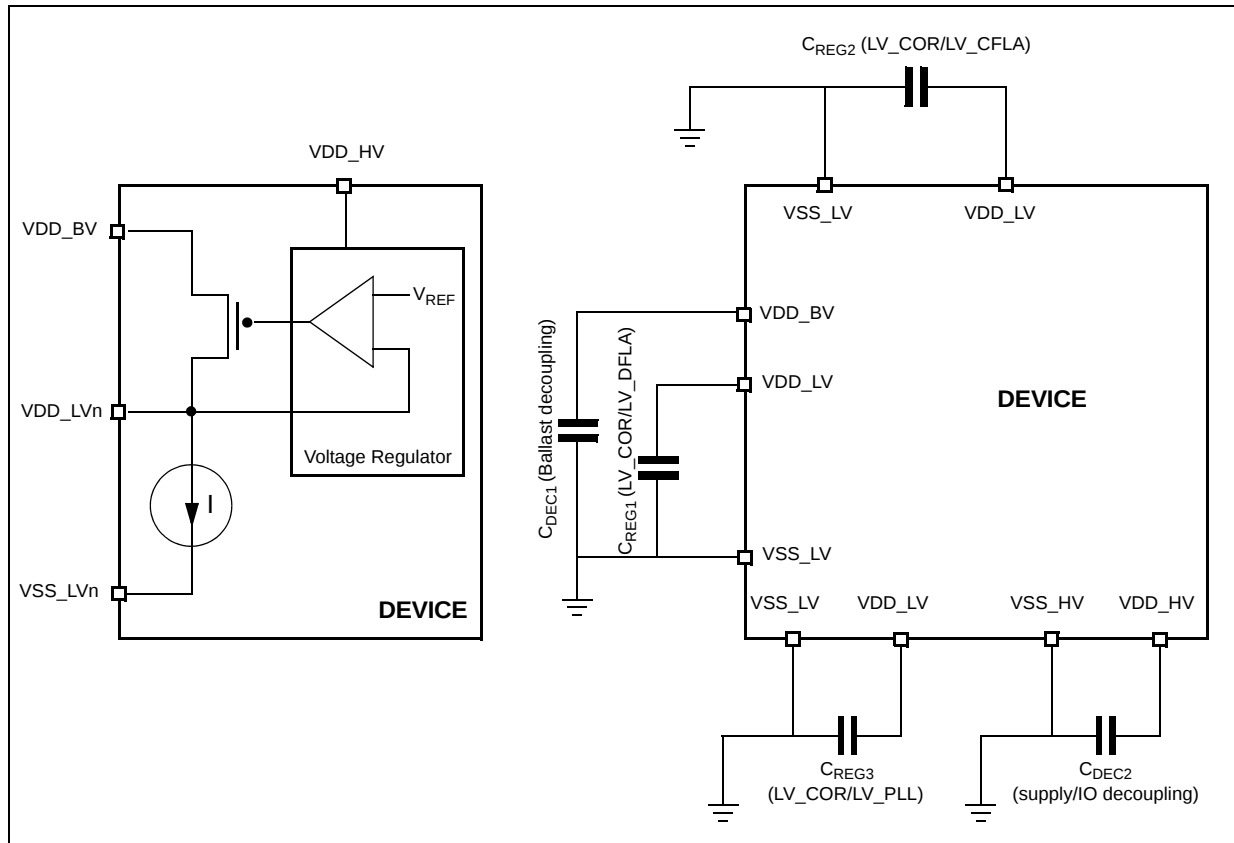
3.17 Power management electrical characteristics

3.17.1 Voltage regulator electrical characteristics

The device implements an internal voltage regulator to generate the low voltage core supply V_{DD_LV} from the high voltage ballast supply V_{DD_BV} . The regulator itself is supplied by the common I/O supply V_{DD} . The following supplies are involved:

- HV—High voltage external power supply for voltage regulator module. This must be provided externally through VDD_HV power pin.
- BV—High voltage external power supply for internal ballast module. This must be provided externally through VDD_BV power pin. Voltage values should be aligned with V_{DD} .
- LV—Low voltage internal power supply for core, FMPLL and flash digital logic. This is generated by the internal voltage regulator but provided outside to connect stability capacitor. It is further split into four main domains to ensure noise isolation between critical LV modules within the device:
 - LV_COR—Low voltage supply for the core. It is also used to provide supply for FMPLL through double bonding.
 - LV_CFLA—Low voltage supply for code flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
 - LV_DFLA—Low voltage supply for data flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
 - LV_PLL—Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

Figure 9. Voltage regulator capacitance connection



The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

Each decoupling capacitor must be placed between each of the three V_{DD_LV}/V_{SS_LV} supply pairs to ensure stable voltage (see [Section 3.13: Recommended operating conditions](#)).

The internal voltage regulator requires a controlled slew rate of both V_{DD_HV} and V_{DD_BV} as described in [Figure 10](#).

Table 26. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
C _{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R _{REG}	SR	—	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	W
C _{DEC1}	SR	—	Decoupling capacitance ⁽²⁾ ballast	V _{DD_BV} /V _{SS_LV} pair: V _{DD_BV} = 4.5 V to 5.5 V	100 ⁽³⁾	470 ⁽⁴⁾	—	nF
				V _{DD_BV} /V _{SS_LV} pair: V _{DD_BV} = 3 V to 3.6 V	400		—	
C _{DEC2}	SR	—	Decoupling capacitance regulator supply	V _{DD} /V _{SS} pair	10	100	—	nF
$\left \frac{dV_{DD}}{dt}\right $	SR	—	Maximum slope on V _{DD}		—	—	250	mV/μs
ΔV _{DD} (STDBY)	SR	—	Maximum instant variation on V _{DD} during standby exit		—	—	30	mV
$\frac{dV_{DD}(\text{STDBY})}{dt}$	SR	—	Maximum slope on V _{DD} during standby exit		—	—	15	mV/μs
V _{MREG}	CC	T	Main regulator output voltage	Before exiting from reset	—	1.32	—	V
		P		After trimming	1.16	1.28	—	
I _{MREG}	SR	—	Main regulator current provided to V _{DD_LV} domain	—	—	—	150	mA
I _{MREGINT}	CC	D	Main regulator module current consumption	I _{MREG} = 200 mA	—	—	2	mA
				I _{MREG} = 0 mA	—	—	1	
V _{LPREG}	CC	P	Low power regulator output voltage	After trimming	1.16	1.28	—	V
I _{LPREG}	SR	—	Low power regulator current provided to V _{DD_LV} domain	—	—	—	15	mA
I _{LPREGINT}	CC	D	Low power regulator module current consumption	I _{LPREG} = 15 mA; T _A = 55 °C	—	—	600	μA
		—		I _{LPREG} = 0 mA; T _A = 55 °C	—	5	—	
V _{ULPREG}	CC	P	Ultra low power regulator output voltage	After trimming	1.16	1.28	—	V

released as soon as internal reset sequence is completed regardless of LVDHV5H threshold.

Table 27. Low voltage detector electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
V _{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V _{PORH}	CC	P	Power-on reset threshold	T _A = 25 °C, after trimming	1.5	—	2.6	
		T		—	1.5	—	2.6	
V _{LVDHV3H}	CC	T	LVDHV3 low voltage detector high threshold	—	—	—	2.95	
V _{LVDHV3L}	CC	P	LVDHV3 low voltage detector low threshold		2.6	—	2.9	
V _{LVDHV5H}	CC	T	LVDHV5 low voltage detector high threshold		—	—	4.5	
V _{LVDHV5L}	CC	P	LVDHV5 low voltage detector low threshold		3.8	—	4.4	
V _{LVDLVCORL}	CC	P	LVDLVCOR low voltage detector low threshold		1.08	—	1.16	
V _{LVDLVBKPL}	CC	P	LVDLVBKP low voltage detector low threshold		1.08	—	1.16	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

3.18 Power consumption

Table 28 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 28. Power consumption on VDD_BV and VDD_HV

Symbol		C	Parameter	Conditions ⁽¹⁾		Value			Unit
						Min	Typ	Max	
I _{DDMAX} ⁽²⁾	CC	D	RUN mode maximum average current	—		—	115	140 ⁽³⁾	mA
I _{DDRUN} ⁽⁴⁾	CC	T	RUN mode typical average current ⁽⁵⁾	f _{CPU} = 8 MHz	—	7	—	mA	
		T		f _{CPU} = 16 MHz	—	18	—		
		T		f _{CPU} = 32 MHz	—	29	—		
		P		f _{CPU} = 48 MHz	—	40	100		
		P		f _{CPU} = 64 MHz	—	51	125		
I _{DDHALT}	CC	C	HALT mode current ⁽⁶⁾	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	8	15	mA
		P			T _A = 125 °C	—	14	25	

Table 31. Flash read access timing

Symbol	C	Parameter	Conditions ⁽¹⁾	Max	Unit
f_{READ}	CC	Maximum frequency for Flash reading	2 wait states	64	MHz
			1 wait state	40	
			0 wait states	20	

1. $V_{\text{DD}} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_{\text{A}} = -40$ to 125 °C, unless otherwise specified

3.19.2 Flash power supply DC characteristics

Table 32 shows the power supply DC characteristics on external supply.

Table 32. Flash memory power supply DC electrical characteristics

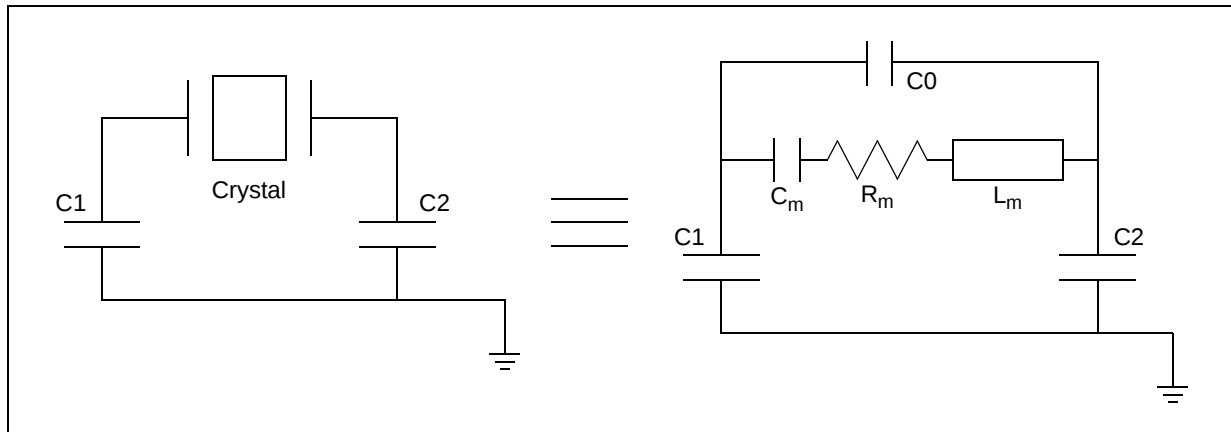
Symbol	C	Parameter	Conditions ⁽¹⁾	Value			Unit
				Min	Typ	Max	
$I_{\text{FREAD}}^{(2)}$	CC	Sum of the current consumption on VDD_HV and VDD_BV on read access	Code flash memory module read $f_{\text{CPU}} = 64 \text{ MHz}^{(3)}$	—	15	33	mA
			Data flash memory module read $f_{\text{CPU}} = 64 \text{ MHz}^{(3)}$	—	15	33	
$I_{\text{FMOD}}^{(2)}$	CC	Sum of the current consumption on VDD_HV and VDD_BV on matrix modification (program/erase)	Program/Erase ongoing while reading code flash memory registers $f_{\text{CPU}} = 64 \text{ MHz}^{(3)}$	—	15	33	mA
			Program/Erase ongoing while reading data flash memory registers $f_{\text{CPU}} = 64 \text{ MHz}^{(3)}$	—	15	33	
I_{FLPW}	CC	Sum of the current consumption on VDD_HV and VDD_BV	During code flash memory low-power mode	—	—	900	μA
			During data flash memory low-power mode	—	—	900	
I_{FPWD}	CC	Sum of the current consumption on VDD_HV and VDD_BV	During code flash memory power-down mode	—	—	150	μA
			During data flash memory power-down mode	—	—	150	

1. $V_{\text{DD}} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_{\text{A}} = -40$ to 125 °C, unless otherwise specified

2. This value is only relative to the actual duration of the read cycle

3. $f_{\text{CPU}} 64 \text{ MHz}$ can be achieved only at up to 105 °C

Figure 16. Equivalent circuit of a quartz crystal

Table 39. Crystal motional characteristics⁽¹⁾

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
L_m	Motional inductance	—	—	11.796	—	KH
C_m	Motional capacitance	—	—	2	—	fF
$C1/C2$	Load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground ⁽²⁾	—	18	—	28	pF
$R_m^{(3)}$	Motional resistance	AC coupled @ $C0 = 2.85$ pF ⁽⁴⁾	—	—	65	kW
		AC coupled @ $C0 = 4.9$ pF ⁽⁴⁾	—	—	50	
		AC coupled @ $C0 = 7.0$ pF ⁽⁴⁾	—	—	35	
		AC coupled @ $C0 = 9.0$ pF ⁽⁴⁾	—	—	30	

1. Crystal used: Epson Toyocom MC306

2. This is the recommended range of load capacitance at OSC32K_XTAL and OSC32K_EXTAL with respect to ground. It includes all the parasitics due to board traces, crystal and package.

3. Maximum ESR (R_m) of the crystal is 50 k Ω

4. $C0$ includes a parasitic capacitance of 2.0 pF between OSC32K_XTAL and OSC32K_EXTAL pins

Figure 17. Slow external crystal oscillator (32 kHz) timing diagram

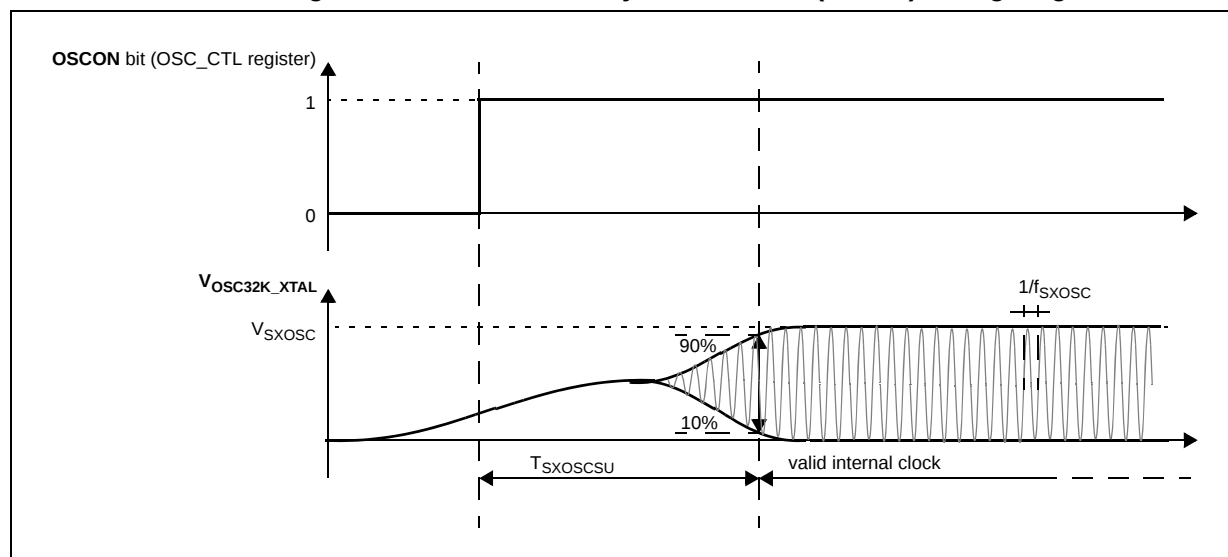


Table 40. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
f _{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
V _{SXOSC}	CC	T	Oscillation amplitude	—	—	2.1	—	V
I _{SXOSCBIAS}	CC	T	Oscillation bias current	—	—	2.5	—	μA
I _{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	8	μA
T _{SXOSCSU}	CC	T	Slow external crystal oscillator start-up time	—	—	—	2 ⁽²⁾	s

1. $V_{DD} = 3.3\text{ V} \pm 10\% / 5.0\text{ V} \pm 10\%$, $T_A = -40$ to $125\text{ }^{\circ}\text{C}$, unless otherwise specified. Values are specified for no neighbor GPIO pin activity. If oscillator is enabled (OSC32K_XTAL and OSC32K_EXTAL pins), neighboring pins should not toggle.

2. Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

3.23 FMPLL electrical characteristics

The device provides a frequency-modulated phase-locked loop (FMPLL) module to generate a fast system clock from the main oscillator driver.

Table 41. FMPLL electrical characteristics

Symbol		C	Parameter	Conditions ⁽¹⁾	Value			Unit
					Min	Typ	Max	
f _{PLLIN}	SR	—	FMPLL reference clock ⁽²⁾	—	4	—	64	MHz
Δ _{PLLIN}	SR	—	FMPLL reference clock duty cycle ⁽²⁾	—	40	—	60	%
f _{PLLOUT}	CC	D	FMPLL output clock frequency	—	16	—	64	MHz

Figure 19. Input equivalent circuit (precise channels)

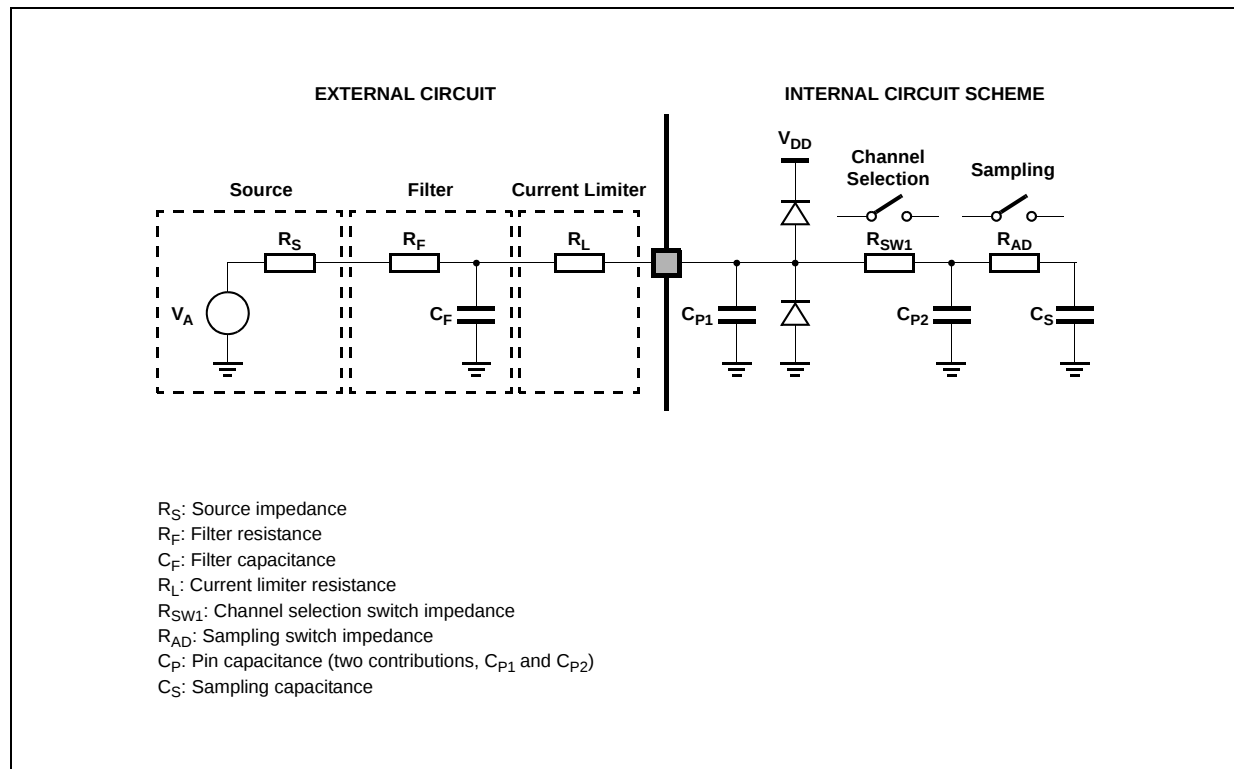
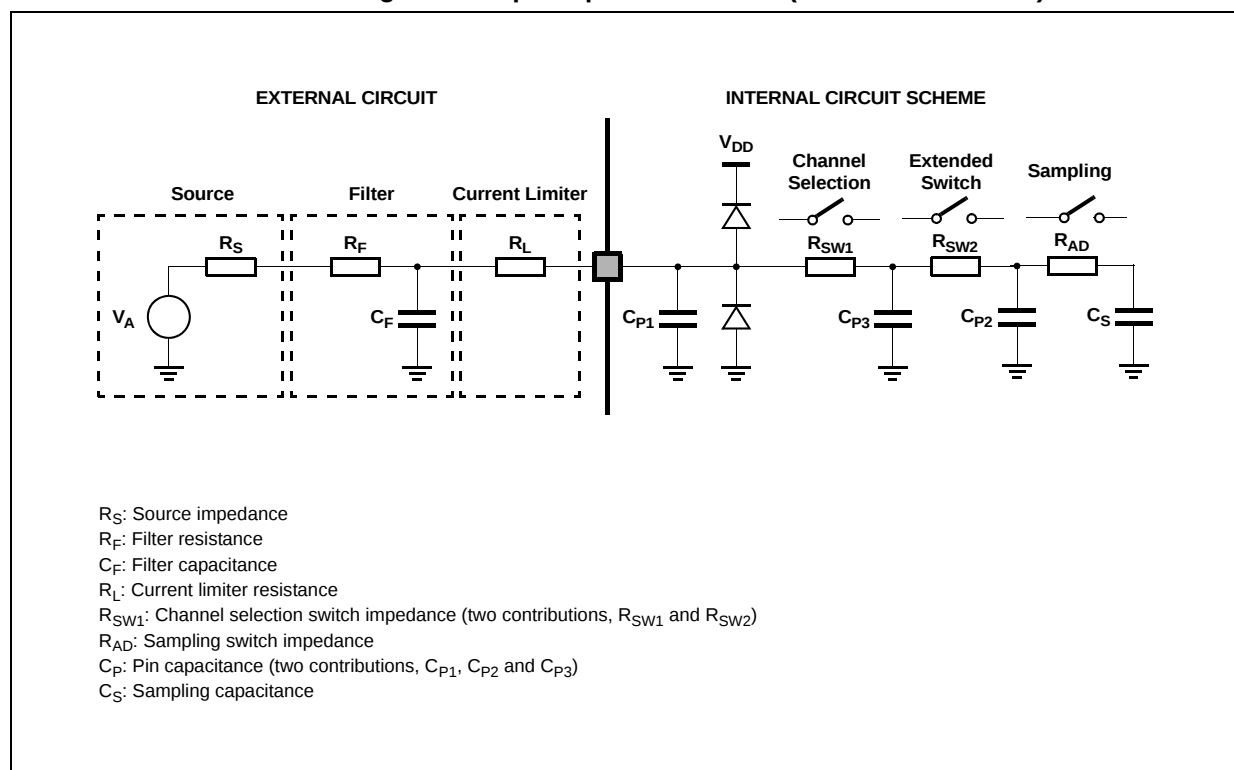


Figure 20. Input equivalent circuit (extended channels)



3.27.4 JTAG characteristics

Table 49. JTAG characteristics

No.	Symbol	C	D	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	15	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t_{TMSS}	CC	D	TMS setup time	15	—	—	ns
5	t_{TMSh}	CC	D	TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns
7	t_{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns

Figure 33. Timing diagram – JTAG boundary scan

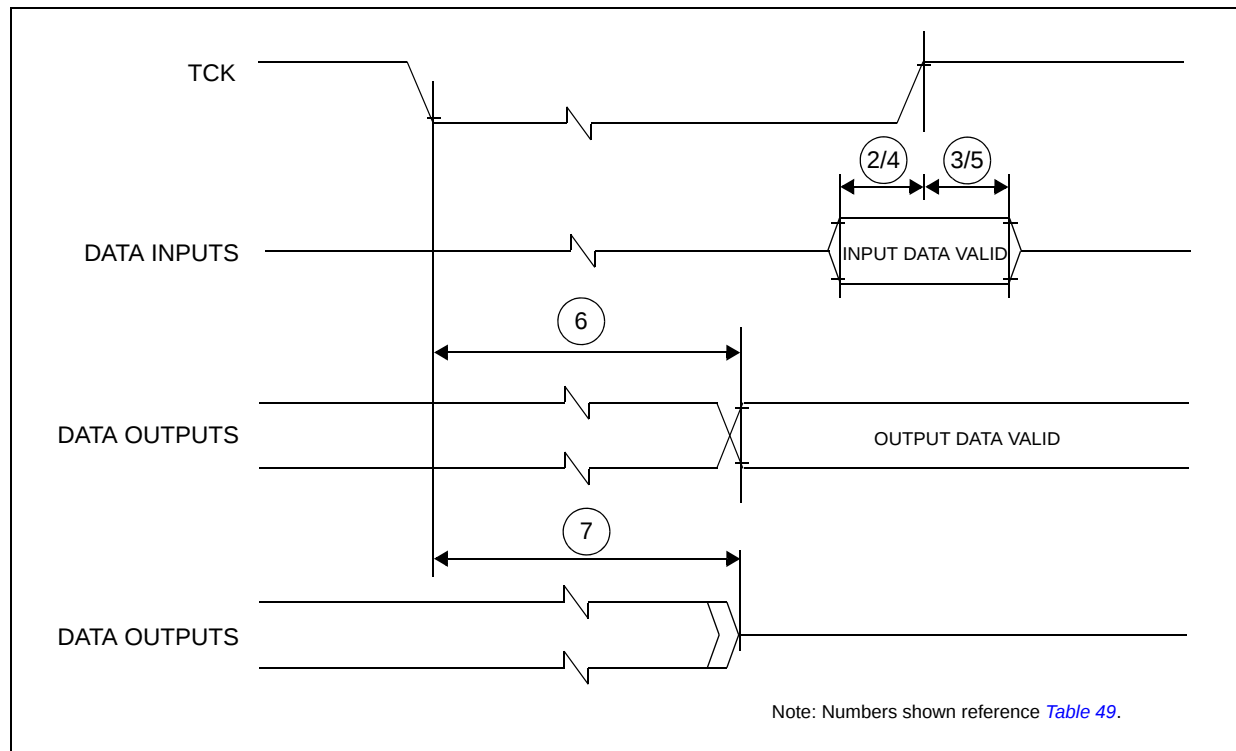


Table 55. Document revision history (continued)

Date	Revision	Changes
22-Jul-2010	7	Changes between revisions 5 and 7 Added LQFP64 package information Updated the "Features" section. Section "Introduction" – Relocated a note Table: "SPC560B40x/50x and SPC560C40x/50x device comparison" – Added footnote regarding SCI and CAN Added eDMA block in the "SPC560B40x/50x and SPC560C40x/50x series block diagram" figure Removed alternate function information from "LQFP 100-pin configuration" and "LQFP 100-pin configuration" figures. Added "Functional port pin descriptions" table Deleted the "NVUSRO[WATCHDOG_EN] field description" section Table: "Absolute maximum ratings" – Removed the min value of V_{IN} relative to V_{DD} Table "Recommended operating conditions (3.3 V)" – TV_{DD}: made single row "Recommended operating conditions (5.0 V)" – deleted T_A C-Grade Part, T_J C-Grade Part, T_A V-Grade Part, T_J V-Grade Part, T_A M-Grade Part, T_J M-Grade Part rows Table: "LQFP thermal characteristics" – Added more rows – Rounded the values Removed table "LBGA208 thermal characteristics" Table "I/O input DC electrical characteristics" – W_{FI}: inserted a footnote – W_{NFI}: inserted a footnote Table "I/O consumption" – Removed I_{DYNSEG} row – Added "I/O weight" table Replaced "nRSTIN" with "RESET" in the "RESET electrical characteristics" section. Table "Voltage regulator electrical characteristics" – Updated the values – Removed $I_{VREGREF}$ and $I_{VREDLVD12}$ – Added a note about I_{DD_BC} Table: "Low voltage monitor electrical characteristics" – changed min value $V_{LVDHV3L}$, from 2.7 to 2.6 – Inserted max value of $V_{LVDLVCORL}$ – Updated V_{PORH} values – Updated $V_{LVDLVCORL}$ value Table "Low voltage power domain electrical characteristics" – Entirely updated Table "Program and erase specifications" – Inserted T_{eslat} row Table "Flash power supply DC electrical characteristics" – Entirely updated